## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applican Applicati Date File Title:	on No.: d:	Richard A. Blanchard Unassigned Filed Herewith DOUBLE DIFFUSED FIELD ON-RESISTANCE	EFFECT TRANSISTOR HAVING REDUCED			
Group A		2811				
Examine	r:	Unassigned				
Docket:		GS 124 D1				
		INFORMATION DISCLO	SURE STATEMENT (IDS)			
P.O. Box	sioner Fo k 1450	r Patents 2231-1450				
SIR:						
reference	es listed	dance with 37 C.F.R. §1.56 and on attached Form PTO/SB/08 and/dideration by the United States Paten	in compliance with 37 C.F.R. §§1.97 and 1.98, the or subsequently identified herein, are being submitted t and Trademark Office.			
I.	COPIES a.☐	A legible copy of (i) each U.S. an	d foreign patents; (ii) each publication or that portion ii) all other information or that portion which caused it			
	b. <b></b>	Any patents, publications or other not enclosed herewith were previous	information which are listed on PTO/SB/08 which are busly cited by or submitted to the PTO in one of the been relied upon for an earlier filing date under 35			
		<u>U.S. Serial Number</u> 09/819,356	<u>U.S. Filing Date</u> 03/28/2001			
II.	<u>CONCI</u> a. ⊠		EVANCE (check at least one box) in (b) of this section, all of the patents, publications or a language (concise explanation not required).			
	b. 🔲		vance of all patents, publications or other information			
	c. 🗌	The following additional information	on is provided for the Examiner's consideration:			
III.	II. CROSS REFERENCE TO RELATED APPLICATION(S)  The Examiner is advised that the following co-pending application(s) contain(s) subject matheat may be related to the present application. By bringing this (these) applications to Examiner's attention, Applicant(s) does(do) not waive the confidentiality provisions of 35 U.S §122.					

Filing Date

Serial No.

Art Unit

## **FEES**

IV. 🛛	THIS ID	OS IS BEING FILED UNDER 37 C.F.R. §1.97(b): (check one box)
	a. 🔀	within three months of the filing date of a national application other than a continued prosecution application under § 1.53(d) (37 C.F.R. §1.97(b)(1)). No fee or statement is required.
	b. 🗌	within three months of the date of entry of the national stage as set forth in § 1.491 in an international application (37 C.F.R. §1.97(b)(2)). No fee or statement is required.
	c.	before the mailing date of a first Office Action on the merits (37 C.F.R. §1.97(b)(3)). No fee or statement is required.
	d.□	before the mailing date of a first Office Action after the filing of a request for continued examination under § 1.114 (37 C.F.R. § 1.97(b)(4)). No fee or statement is required.
v. 🗌	before t Allowar applicat a	DS IS BEING FILED UNDER 37 C.F.R. §1.97(c): (check one box) the mailing date of any of a Final Office Action under 37 C.F.R. §1.113, a Notice of accounder 37 C.F.R. §1.311, or an action that otherwise closes prosecution in the ion (See 37 C.F.R. §1.97(c)).  No statement; therefore, charge deposit account 50-1047 the fee set forth in 37 C.F.R. §1.17(p).
	b. <u></u>	See the statement below. No fee is required.
VI. 🗌		OS IS BEING FILED UNDER 37 C.F.R. §1.97(d):  fore payment of the issue fee and is accompanied by the following:  a statement under 37 C.F.R. §1.97(e) as provided below; and  charge deposit account 50-1047 the petition fee set forth in §1.17(p).
VII. 🔲	·	MENT UNDER 37 C.F.R. §1.97(e) (check only one box, if applicable)
V 11.		lersigned hereby states that each item of information contained in the IDS was cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of IDS; or
	b	no item of information contained in the IDS was cited in a communication from a foreign Patent Office in a counterpart foreign application, and to knowledge of the person signing the statement after making reasonable inquiry, no item of information contained in the IDS was known to any individual designated in 37 C.F.R. 1.56(c) more than three months prior to the filing of this statement, or
	с.	some of the items of information contained in the IDS were cited in a communication from a foreign Patent Office. As to this information, the undersigned states that each item of information contained in the IDS was cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this IDS. As to the remaining information, the undersigned hereby states that no item of this remaining information contained in the IDS was cited in a communication from a foreign Patent Office in a counterpart foreign application or, to the knowledge of the person signing the statement after making reasonable inquiry, no item of information contained in the IDS was known to any individual designated in 37 C.F.R. 1.56(c) more than three months prior to the filing of this statement.
VIII.	PAYMI	ENT OF FEES  A check in the amount of is enclosed for the above-identified fee(s).
	Ï	Please charge Deposit Account No. 50-1047 in the amount of \$180.00 for the above-indicated fee(s).
	$\boxtimes$	If Applicant has overlooked any additional fees, or if any overpayment has been made, the Commissioner is hereby authorized to credit or debit Deposit Account 50-1047.
		Two Copies of this paper are attached for Deposit Account charges and debits.

It is Applicant(s)' opinion that the claims presently on file patently distinguish the present invention from each of these references. The above references are being cited only in the interests of candor and without any admission that they constitute statutory prior art or contain matter which anticipates the invention or which would render the same obvious, either singly or in a combination, to a person of ordinary skill in the art.

If the Examiner has any questions concerning this IDS, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 50-1047.

Respectfully submitted, Mayer Fortkort & Williams, PC

Kurm L. Williams Attorney for Applicant Reg. No. 36,721 Tel. 908-518-7700 Miains

Mayer Fortkor Customer Nun		
Enclosures:		PTO/SB/08 References Foreign Search Report Other:
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	ma	mi Dianati

(Signature)

Docket No.: GS 124 D1

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Substitute fo	or form 1449A/PTO			Co.	Complete if Known		
				Application Number	Unassigned		
INFORM	<b>1ATION DISC</b>	LOSURE		Filing Date	Filed Herewith		
STATEM	MENT BY APP	LICANT		First Named Inventor	Richard A. Blanchard		
				Group Art Unit	2811		
(use as man)	y sheets as necessar	v)		Examiner Name	Unassigned		
Sheet	1	of	2	Attorney Docket Number	GS 124 D1		

Examiner	Cite	U.S. Patent Document		Name of Patentee or	Date of Publication of Cited Document MM-
Initials*	No. 1	Number	Class/Subclass	Applicant of Cited Document	DD-YYYY
	1	6,274,464 B2	438/507	Drobny et al.	08-2001
	2	6,084,268	257/342	De Fresart et al.	07-04-2000
	3	5,981,344	438/270	Hshieh et al.	11-09-1999
	4	5,893,742	438/507	Demirliogluy et al.	04-1999
	5	5,814,858	257/328	Williams	09-1998
	6	5,072,266	257/330	Bulucea et al.	12-10-1991
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Examiner	Cite		Foreign Patent Do	cument	Name of Patentee or	Date of Publication of Cited Document	T
Initials*	No. 1	o. 1 Office <sup>3</sup> Number	Class/	Applicant of Cited	MM-DD-YYYY		
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Examiner	<u>'</u>			•	Date		
Signature				_	Considered		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English Language Translation is attached.

Docket No.: GS 124 D1

Substitute for	form 1449A/PTO		= '	Col	Complete if Known		
				Application Number	Unassigned		
INFORMA	ATION DISCLO	OSURE		Filing Date	Filed Herewith		
STATEME	ENT BY APPLI	CANT		First Named Inventor	Richard A. Blanchard		
				Group Art Unit	2811		
(use as many s	heets as necessary)			Examiner Name	Unassigned		
Sheet	2	of	2	Attorney Docket Number	GS 124 D1		

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	T <sup>2</sup>				
Examiner Initials*	No. magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
-	1	Baliga, B. Jayant, Chapter 7, "Power Mosfet: 7.1 Basic Structure and Operation," PWS Publishing (Boston, 1996), pp. 336-339.					
	2	Wolf, Stanley et al., "Silicon Processing for the VLSI Era", Vol. 1: Process Technology," Lattice Press, Sunset Beach, CA, (1986), pp. 321-323.					
	3	Wilson, Syd R., et al., "Handbook of Multilevel Metallization for Integrated Circuits," Noyes Publ., Westwood, New Jersey, (1993), pp. 42-59; 867-872.					
	4	IBM Technical Disclosure Bulletin, "Fabrication of Narrow Self Aligned Trenches and Isolated N-Type Silicon Region With buried N+ Layer," Vol. 34, No. 10A, (March, 1992), pp. 397-399.					
_	5	Gary E. McGuire, "Semiconductor Materials and Process Technology Handbook,' Noyes Publ., Norwich, New York, (1988), p.18.					
	6	Hu, Chenning, "Optimum Doping Profile for Minimum Ohmic Resistance and High-Breakdown Voltage," IEEE Transactions on Electron Devices, Vol. ED-26, No. 3, March 1979, pp. 243-244.					
	7	Grove, A. S., Physics and Technology of Semiconductor Devices, 3.7, "The Redistribution of Impurities in Epitaxial Growth," pp. 78-83, John Wiley and Sons, Inc. New York, 1967.					

Examiner	Date	
Signature	Considered	

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